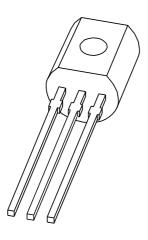
DISCRETE SEMICONDUCTORS

DATA SHEET



2N4401 NPN switching transistor

Product specification Supersedes data of 1999 Apr 23 2004 Oct 28





NPN switching transistor

2N4401

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

• Industrial and consumer switching applications.

DESCRIPTION

NPN switching transistor in a TO-92; SOT54 plastic package. PNP complement: 2N4403.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter

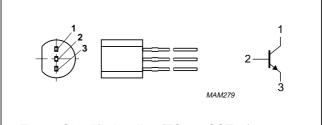


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

ORDERING INFORMATION

TYPE NUMBER		PACKAGE					
ITPE NOWIBER	NAME	DESCRIPTION	VERSION				
2N4401	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	600	mA
I _{CM}	peak collector current		_	800	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	630	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

2N4401

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	200	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

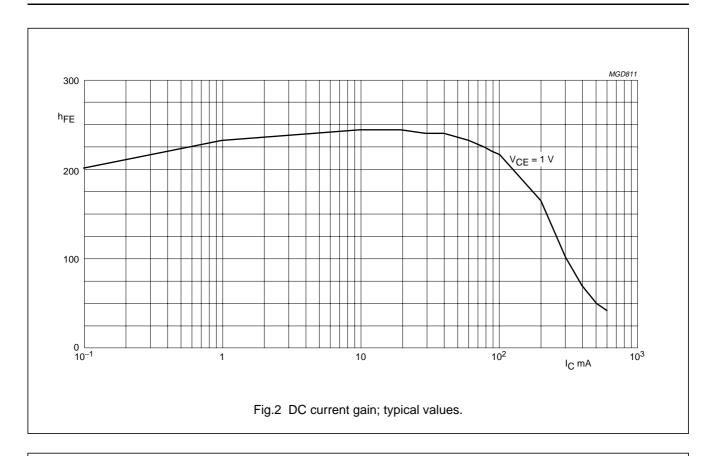
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 60 V; I _E = 0 A	_	50	nA
I _{EBO}	emitter-base cut-off current	mitter-base cut-off current $V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$		50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; see Fig.2			
		I _C = 0.1 mA	20	_	
		I _C = 1 mA	40	_	
		I _C = 10 mA	80	_	
		I _C = 150 mA; note 1	100	300	
		V _{CE} = 2 V; I _C = 500 mA; note 1	40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	400	mV
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; \text{ note 1}$	_	750	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	950	mV
		I _C = 500 mA; I _B = 50 mA; note 1	_	1.2	V
C _c	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	6.5	pF
C _e	emitter capacitance	$V_{EB} = 500 \text{ mV}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	_	30	pF
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 20 \text{ mA}; f = 100 \text{ MHz}$	250	_	MHz
Switching	times (between 10 % and 90 % leve	els); see Fig.3			•
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	_	35	ns
t _d	delay time	I _{Boff} = -15 mA	_	15	ns
t _r	rise time		_	20	ns
t _{off}	turn-off time		_	250	ns
t _s	storage time		_	200	ns
t _f	fall time		_	60	ns

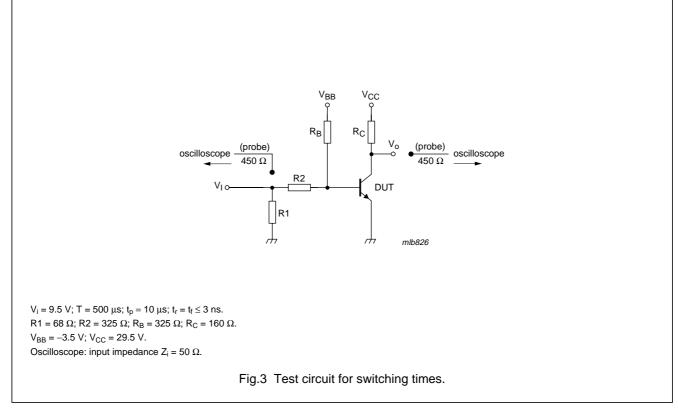
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN switching transistor

2N4401





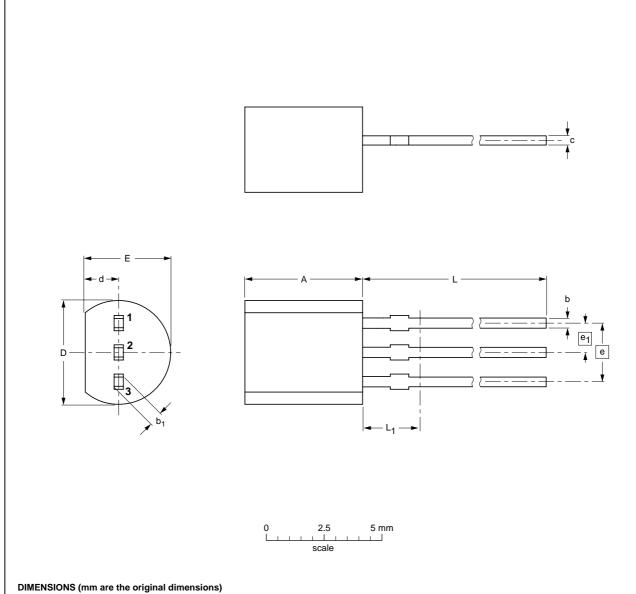
NPN switching transistor

2N4401

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE
VERSION	ON IEC JEDEC JEITA PRO		PROJECTION	ISSUE DATE		
SOT54		TO-92	SC-43A			97-02-28 04-06-28

2004 Oct 28 5

NPN switching transistor

2N4401

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2004

SCA76

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Oct 28

Document order number: 9397 750 13546

Let's make things better.

Philips Semiconductors



